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concl.  
value, which when [multiplied] divided by the stored coefficient, yields the absolute reflectance value of the unknown material. A✓

Col. 1, line 60: amend the first five lines of this paragraph as follows: --FIG. 1 illustrates a typical microscope for measuring reflectance in the ultraviolet range. Since the material used in the construction of typical refractive lenses [is chromatic or] is opaque to UV radiation, [only] reflective optical devices [may] should be used. Hence, a UV source✓

Col. 2, line 60: delete "and multiplication".

IN THE CLAIMS

Rewrite Claim 6 as follows:

6. The method claimed in ~~Claim 1~~ wherein said known material is an aluminum specimen.

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Claim 7, line 1, after "Claim" delete "6" and insert --1-- therefor.

REMARKS

These remarks address the Examiner's comments in the Office Action. Claims 1-5, 7 and a rewritten Claim 6 remain in this application. Claims 1-5 and 7 have been indicated as being allowable if rewritten or amended to overcome the rejection under 35 U.S.C. §112. An Information Disclosure Statement was forwarded as part 7. of the Reissue Application Transmittal. Copies of the references were furnished. Inadvertently, a Form 1449 was not included in the Transmittal. It is requested that the Examiner return an initialled copy of the enclosed Form 1449 to Applicant.

Claims 1-5 and 7 stand rejected based on a defective reissue declaration under 35 U.S.C. § 251 (37 C.F.R. §1.175). Enclosed herewith is a Substitute Declaration for Reissue Application by Mr. Vincent J. Coates, inventor and Chief Executive Officer of the Assignee Nanometrics Incorporated which fully sets forth what the errors are, how they arose and when they were discovered. Thus, each of the matters re the

defective declaration are readily seen to be satisfied in the Substitute Declaration for Reissue Application. The corroborating Declaration of Mr. Lin supports the Declaration of Mr. Coates.

By the amendment above the applicant has deleted the descriptive material that had been added in the reissue application at Column 1, line 38 and has reinserted "aluminum specimen" into the specification to overcome the rejection based on new matter. Rewritten Claim 6 is directed to the aluminum specimen species.

Claims 1-5 and 7 stand rejected under 35 U.S.C. § 112 first paragraph for the reasons set forth in the new matter objections to the specification. The new matter material sought to be added has been deleted. The § 112 rejection of the claims is now moot. In view of the new matter deletion, it is submitted that the rejection has been overcome and no rewriting or amendment to Claim 1 appears needed. The dependency of Claim 7 has been changed to reflect the rewriting of Claim 6. The correction of the errors as enumerated in the Substitute Declaration and as shown in the revised Reissue cut-up do not involve new matter. Each error, as attested to in the corroborating Declaration of Mr. Lin, was such that one would appreciate not only the existence of the error, but what the error was and what its correction would be. This is a test for new matter as set forth in In re Oda et al. 170 USPQ 268, 272 (CCPA 1971). Further, reference is made to Ex parte Marsili et al. 214 USPQ 904 (PTOBA 1979) where a change in a structural formula was held not to be new matter. Further, the Board in Ex parte Marsili et al. at 906 at the bottom of the second column stated as "persuasive" and logical a quote from Appellants' Reply Brief namely,

"No one derives any benefit from an erroneous statement - neither applicants nor the public."

It is submitted that this Amendment together with the accompanying Substitute Reissue Declaration by the Applicant places the Reissue Application in condition for allowance. It

is respectfully requested that, upon such allowance, all the references cited in the original patent and by the Applicant in the Information Disclosure Statement included as part of the Reissue Application be printed on the Reissue Patent.

Allowance of this application for reissue is requested.

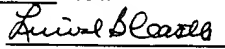
Respectfully submitted,



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I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C., 20231, on March 31, 1994.

03/31/94  
Date of Signature

  
Attorney for Applicant(s)

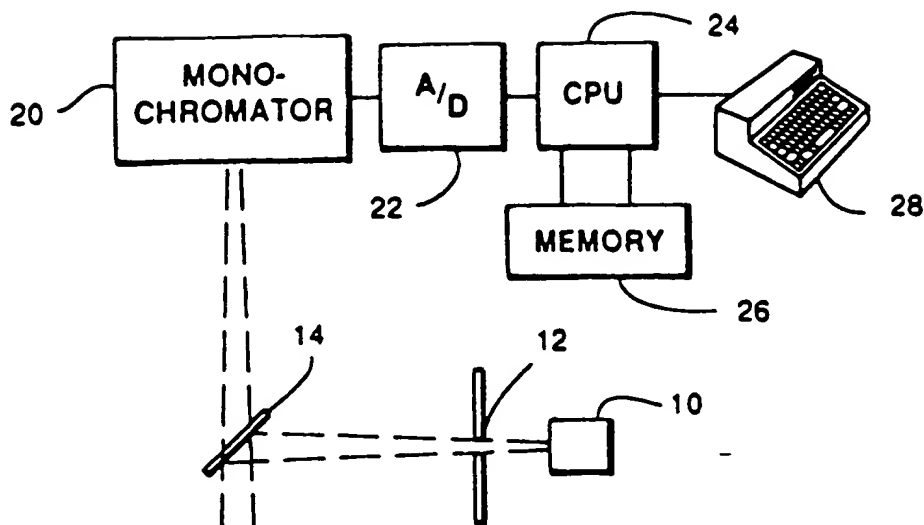


Figure 1

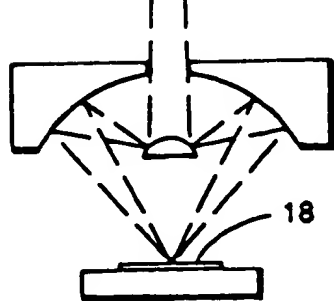
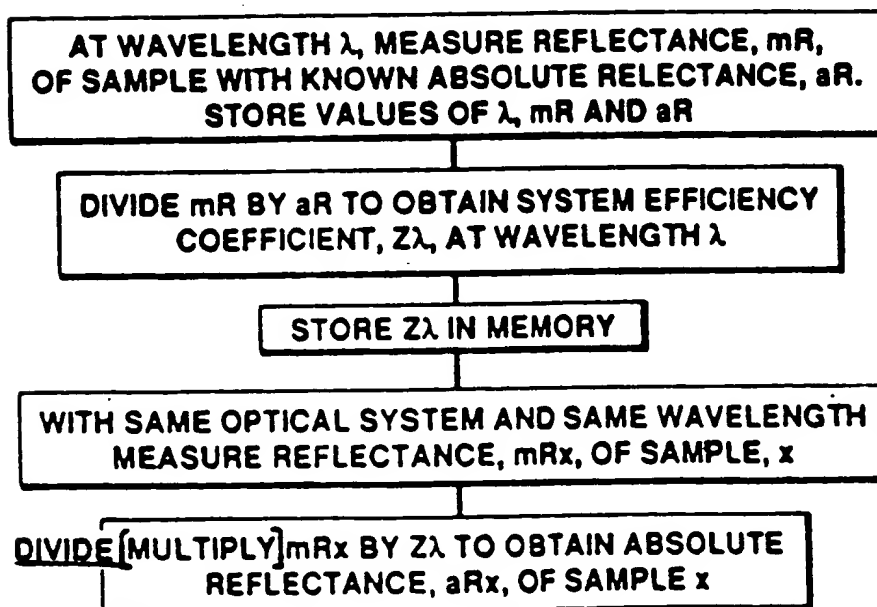


Figure 2



[57]

#### ABSTRACT

A method for determining a value of absolute reflectance of a material at a ~~predetermined~~ desired wavelength, in the ultraviolet range from its measured reflectance which includes system losses contributed by optics, illumination sources, detectors, etc. The method involves the measurement of reflectance from a known material such as single crystal silicon whose absolute reflectance is well known, dividing the measured value by the absolute value to obtain a system efficiency coefficient at the known wavelength and then, without changing the illumination or optics, measuring the reflectance of the unknown material and applying this coefficient to this measured value to obtain its absolute value.

# METHOD FOR DETERMINING ABSOLUTE REFLECTANCE OF A MATERIAL IN THE ULTRAVIOLET RANGE

## BRIEF SUMMARY OF THE INVENTION

This invention relates to the determination of reflectance from a material and particularly to the determination of absolute reflectance independent of losses in an associated optical system.

Some materials are transparent with very little incident energy being reflected from the surface and some materials are opaque and absorb nearly all incident energy and reflect very little. In many materials the ratio of incident energy to reflected energy, or reflectance, varies according to the wavelength of the incident radiation. For example, silicon as used in electronic microcircuits is transparent to infrared wavelengths, translucent between about one micron and infrared, and opaque to ultraviolet radiation.

It is often necessary to determine the energy absorption of some material with unknown chemical contents. An accurate value for absorption can easily be computed from a knowledge of the absolute reflectance from the unknown material since the incident energy can only be divided into absorption and reflectance. But a value for absolute reflectance is not readily obtainable since any measured value of reflectance at some predetermined wavelength is contaminated by losses contributed by the system optics, such as absorption of lenses, illumination sources, beamsplitters, gratings, detectors, etc., all of which also vary with wavelengths.

The object of this invention is to determine the absolute reflectance value of a test material at a desired wavelength, from a measured value of reflectance.

Briefly described, the method involves the steps of measuring the reflectance of a known material, such as single crystal silicon or aluminum specimen, at the desired wavelength, computing the value of absolute reflectance from the index of refraction and absorption data available in [myriads of] handbooks, and then dividing the absolute value by into the measured value to derive a product which is the system efficiency coefficient [of all optical system] coefficients. This value of the coefficient is stored. An unknown material is then tested with the same unchanged optical system and at the same wavelength to obtain a measured reflectance value which, when [multiplied] divided by the stored coefficient, yields the absolute reflectance value of the unknown material.

## BRIEF DESCRIPTION OF THE DRAWINGS

In the drawings which illustrate the preferred embodiment of the invention:

FIG. 1 is a schematic drawing illustrating a reflective microscope and detector processing apparatus for ultraviolet examinations; and

FIG. 2 illustrate the steps for determining absolute reflectance of an unknown material.

## DETAILED DESCRIPTION

FIG. 1 illustrates a typical microscope for measuring reflectance in the ultraviolet range. Since the material used in the construction of typical refractive lenses is [chromatic or] opaque to UV radiation, only reflective optical devices [may] should be used. Hence, a UV source with known output energy, such as a deuterium discharge tube, with output beam condensed by a small iris is reflected from a planar quartz beam splitter into a reflective objective lens which focuses the UV

beam onto a specimen 18. The image from the specimen 18 is magnified by the reflective objective and, after passing through the planar quartz beam splitter 14, is focused into a monochromator 20 where the image beam is passed through a narrow slit to isolate a narrow band of wavelengths before detection.

The detected image beam, after being converted by an analog-to-digital converter 22, is applied to a computer 24 having a memory 26 and an input-output device 28, such as a keyboard terminal.

When the microscope system of FIG. 1 is used for measuring reflectances, all optical elements such as the beam splitter 14, the several reflective surfaces of the objective lens 16 and the internal optical elements in the monochromator 20, absorb energy from the incident radiating beam of the source 10. Further, the absorbed energy varies with variations in the incident wavelength.

A value of reflectance can easily be measured with the microscope system, but that is a measured reflectance,  $mR$ , which has little value since it includes the unknown system losses resulting from the energy absorption of the optical elements. The type of reflectance of value is the absolute reflectance,  $aR$ , the ratio of reflected energy to incident energy, independent of system losses.

Absolute reflectance of an unknown material can be determined if one knows the values of both absolute and measured reflectance of a known material at the desired wavelength. With this data, the system losses, or system efficiency coefficient,  $Z\lambda$ , at wavelength  $\lambda$ , is computed by merely dividing the measured value by the absolute value of reflectance. Many reference books list tables of refractive index and absorption of various materials at various frequencies and many also list the values of absolute reflectance at various wavelengths. Thus, absolute reflectance values,  $aR$ , are available or calculable for several pure materials, such as single crystal silicon.

With knowledge of an absolute reflectance value,  $aR$ , of a particular pure material at some known wavelength  $\lambda$ , the system efficiency coefficient,  $Z\lambda$  at that wavelength, is determined by measuring the measured reflectance,  $mR$ , and dividing by  $aR$ :

$$Z\lambda = mR/aR \quad (1)$$

To determine the absolute reflectance,  $aRx$ , of a material,  $x$ , measure the measured reflectance,  $mRx$ , of that unknown material,  $x$ , at the same wavelength,  $\lambda$ , and with the same optical system, and multiply divide the results by the system efficiency coefficient,  $Z\lambda$ .

$$aRx = mRx(Z\lambda) \quad aRx = mRx/Z\lambda \quad (2)$$

The determination of absolute reflectance can readily be performed by the computer system illustrated in FIG. 1. The value  $aR$  of the known material at the predetermined wavelength is entered through the keyboard 28 into the computer 24 which is programmed to perform the simple division and multiplication shown in Equations (1) and (2) above. The value,  $aR$  is stored in the memory 26. The reflectance,  $mR$  is then measured of the known material 18 on the microscope stage and the detected value is stored into the memory 26. The computer 24 then performs Equation (1) and stores the efficiency coefficient,  $Z\lambda$  in memory. Without making any changes in the energy source or the optical system, the known material 18 is replaced with the unknown

material,  $x$ , and the reflectivity is measured to obtain the value,  $mRx$ , which is applied to the computer 24 along with the efficiency coefficient  $Z\lambda$ , in memory. The computer performs the multiplication division of Equation (2) to obtain the absolute reflectance,  $aRx$  of the unknown material,  $x$ .

I claim:

1. A method for determining an absolute reflectance of material from a microscopic measurement of its measured reflectance in the ultraviolet radiation range, said method comprising the steps of:

determining a value of absolute reflectance of a known material at a predetermined wavelength;

measuring the reflectance of said known material to obtain a value of measured reflectance with a microscope illuminated with radiation at said predetermined wavelength;

with said values of absolute reflectance and measured reflectance, calculating an efficiency coefficient representing all absorption and losses caused by the microscope optical system, its reflectance detectors and its illumination system at said predetermined wavelength;



measuring the reflectance of an unknown material to obtain a second value of measured reflectance with said microscope illuminated with said radiation at said predetermined wavelength;

- 5 applying said efficiency coefficient to said second value of measured reflectance to obtain a value of absolute reflectance of said unknown material.

2. The method claimed in claim 1 wherein said step of applying includes the step of ~~multiplying~~ dividing said second  
10 value by said efficiency coefficient.

3. The method claimed in claim 2 wherein said microscope is a reflecting microscope.

4. The method claimed in claim 3 wherein said predetermined wavelength is in the ultraviolet radiation  
15 range.

5. The method claimed in claim 2 wherein the determined values of absolute reflectance of said known material, said value of measured reflectance of said known material and said value of measured reflectance  
20 of said unknown material are stored in a memory of a computer that performs the step of calculating said efficiency coefficient and said value of absolute reflectance of said unknown material.

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6. The method claimed in Claim 1 wherein said known material is an  
35 aluminum specimen.

7. The method claimed in Claim 1 wherein said known material is  
40 single crystal silicon.

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